

confid
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mixed crystal, reference should be made to the United States Patent 5,352,912.

IN THE CLAIMS

Please amend claim 3 as follows:

3. (Amended) A heterobipolar transistor, comprising:

a substrate;

a collector layer formed on said substrate;

a base layer formed on said collector layer; and

an emitter layer formed on said base layer,

said base layer comprising a SiGeC ternary mixed crystal having a C concentration profile such that a C concentration in said base layer increases from a first interface facing said emitter layer to a second interface facing said collector layer,

wherein said base layer has a Ge concentration substantially constant from said first interface to said second interface.